

## Product Summary

- Continuous Drain Source Voltage: 60V
- On-State Resistance: 500mΩ
- Nominal Load Current ( $V_{IN} = 5V$ ): 1.3A
- Clamping Energy: 90mJ

## Description

The DIODES™ ZXMS6004FFQ is a self-protected low side IntelliFET™ MOSFET with logic level input. It integrates overtemperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6004FFQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

## Applications

- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- $\mu C$  compatible power switch for 12V and 24V DC applications
- Automotive rated
- Replaces electromechanical relays and discrete circuits
- Linear mode capability – the current-limiting protection circuitry is designed to de-activate at low  $V_{DS}$  to minimize on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low  $V_{DS}$ .

## Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- High Continuous Current Rating
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The ZXMS6004FFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

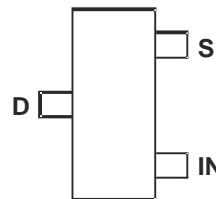
## Mechanical Data

- Package: SOT23F
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish<sup>(e3)</sup>
- Weight: 0.012 grams (Approximate)

SOT23F



Top View



Top view  
Pin Out

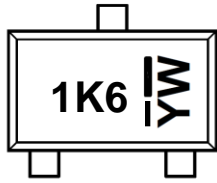
## Ordering Information (Note 4)

| Part Number   | Package | Marking | Reel Size (inches) | Tape Width (mm) | Packing |         |
|---------------|---------|---------|--------------------|-----------------|---------|---------|
|               |         |         |                    |                 | Qty.    | Carrier |
| ZXMS6004FFQTA | SOT23F  | 1K6     | 7                  | 12              | 3,000   | Reel    |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

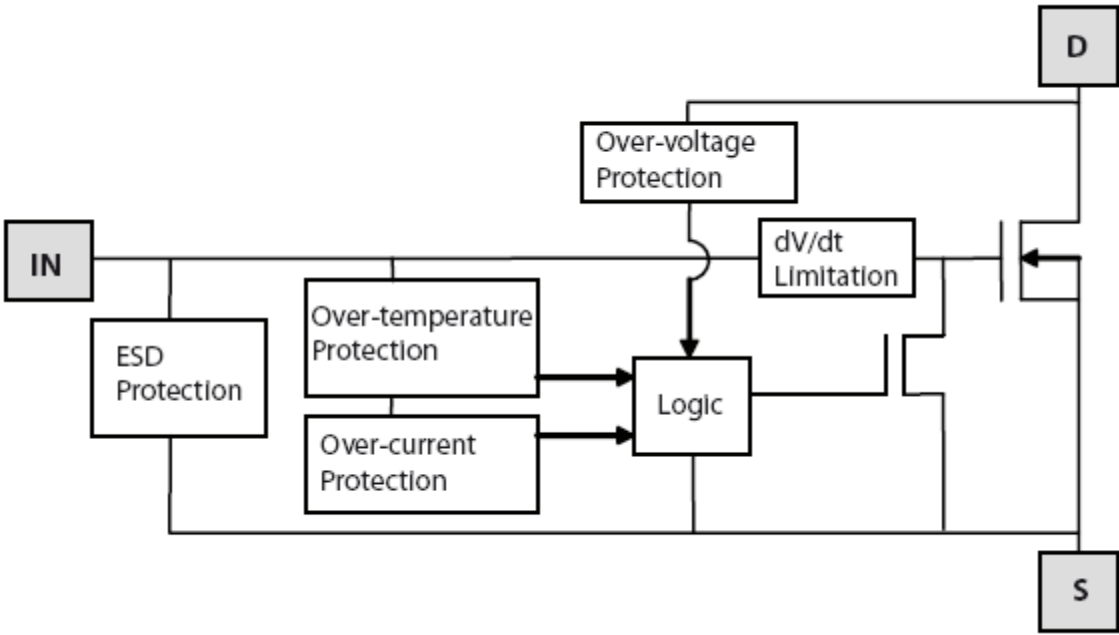
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**Marking Information**



1K6 = Product Type Marking Code  
 Y or  $\bar{Y}$ : Year: 0 to 9  
 W or  $\bar{W}$ : Week: A to Z: 1 to 26  
           a to z: 27 to 52  
 z: Represents 52 & 53 Week

**Functional Block Diagram**



**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol              | Value                              | Unit |
|--|---------------------|------------------------------------|------|
| Continuous Drain-Source Voltage  | V <sub>DS</sub>     | 60                                 | V    |
| Drain-Source Voltage for Short Circuit Protection  | V <sub>DS(SC)</sub> | 36                                 | V    |
| Continuous Input Voltage   | V <sub>IN</sub>     | -0.5 ... +6                        | V    |
| Continuous Input Current @ -0.2V ≤ V <sub>IN</sub> ≤ 6V  | I <sub>IN</sub>     | No Limit<br> I <sub>IN</sub>   ≤ 2 | mA   |
| Continuous Input Current @ V <sub>IN</sub> < -0.2V or V <sub>IN</sub> > 6V                                       |                     |                                    |      |
| Pulsed Drain Current @ V <sub>IN</sub> = 3.3V  | I <sub>DM</sub>     | 2                                  | A    |
| Pulsed Drain Current @ V <sub>IN</sub> = 5V  | I <sub>DM</sub>     | 2.5                                | A    |
| Continuous Source Current (Body Diode)   | I <sub>S</sub>      | 1                                  | A    |
| Pulsed Source Current (Body Diode)   | I <sub>SM</sub>     | 5                                  | A    |
| Unclamped Single Pulse Inductive Energy,<br>T <sub>J</sub> = +25°C, I <sub>D</sub> = 0.5A, V <sub>DD</sub> = 24V | E <sub>AS</sub>     | 90                                 | mJ   |
| Electrostatic Discharge (Human Body Model)   | V <sub>ESD</sub>    | 4,000                              | V    |
| Charged Device Model   | V <sub>CDM</sub>    | 1,000                              | V    |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                     | Symbol           | Value       | Unit  |
|--|------------------|-------------|-------|
| Power Dissipation @T <sub>A</sub> = +25°C (Note 5) | P <sub>D</sub>   | 0.83        | W     |
| Linear Derating Factor                             |                  | 6.66        | mW/°C |
| Power Dissipation @T <sub>A</sub> = +25°C (Note 6) | P <sub>D</sub>   | 1.5         | W     |
| Linear Derating Factor                             |                  | 12.0        | mW/°C |
| Thermal Resistance, Junction to Ambient (Note 5)   | R <sub>θJA</sub> | 150         | °C/W  |
| Thermal Resistance, Junction to Ambient (Note 6)   | R <sub>θJA</sub> | 83          | °C/W  |
| Thermal Resistance, Junction to Case (Note 7)      | R <sub>θJC</sub> | 44          | °C/W  |
| Operating Temperature Range                        | T <sub>J</sub>   | -40 to +150 | °C    |
| Storage Temperature Range                          | T <sub>STG</sub> | -55 to +150 | °C    |

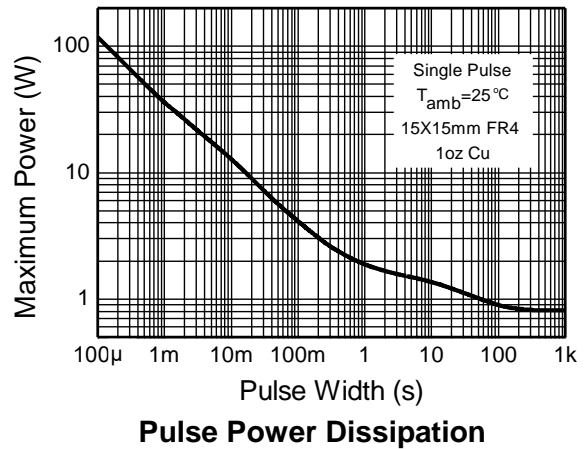
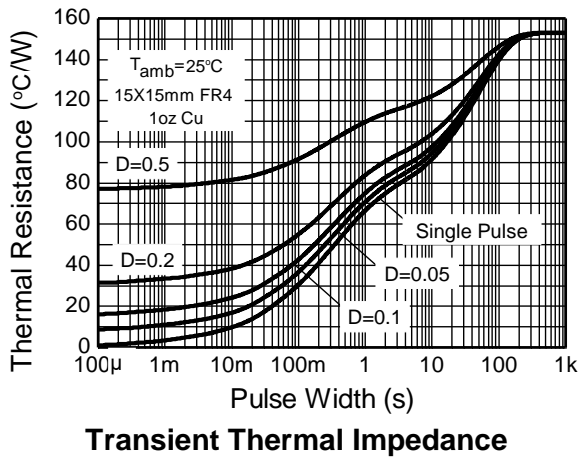
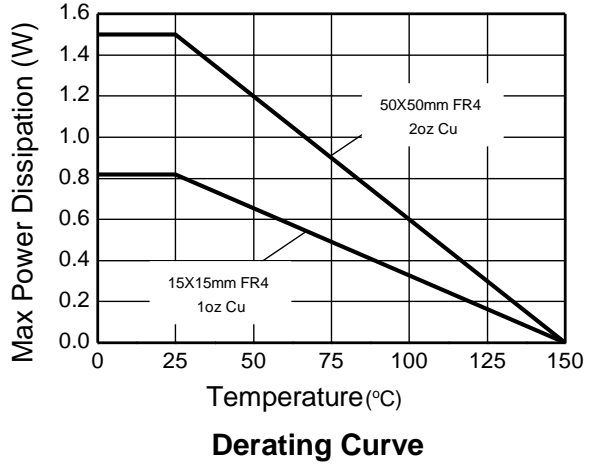
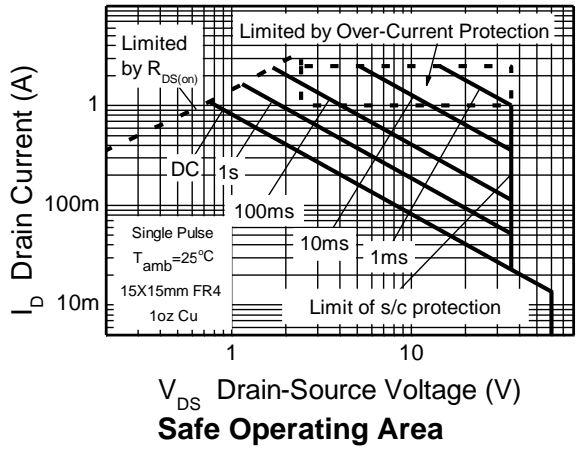
**Recommended Operating Conditions**

The ZXMS6004FFQ is optimized for use with μC operating from 3.3V and 5V supplies.

| Characteristic  | Symbol          | Min | Max  | Unit |
|---|-----------------|-----|------|------|
| Input Voltage Range   | V <sub>IN</sub> | 0   | 5.5  | V    |
| Ambient Temperature Range                                     | T <sub>A</sub>  | -40 | +125 | °C   |
| High Level Input Voltage for MOSFET to be On                  | V <sub>IH</sub> | 3   | 5.5  | V    |
| Low Level Input Voltage for MOSFET to be Off                  | V <sub>IL</sub> | 0   | 0.7  | V    |
| Peripheral Supply Voltage (Voltage to Which Load is Referred) | V <sub>P</sub>  | 0   | 36   | V    |

- Notes:
5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions.
  6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
  7. Thermal resistance from junction and the mounting surfaces of the drain pins.

**Typical Thermal Characteristics**

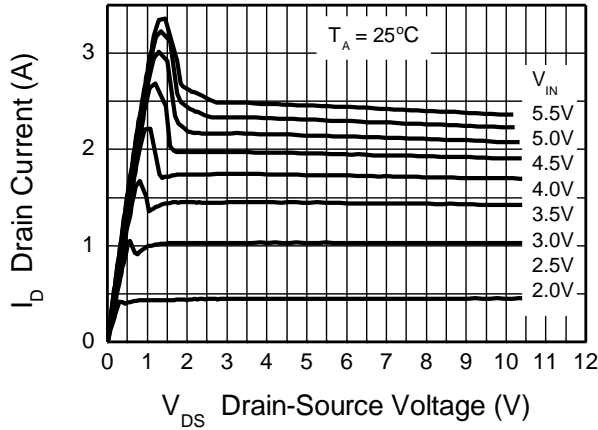


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

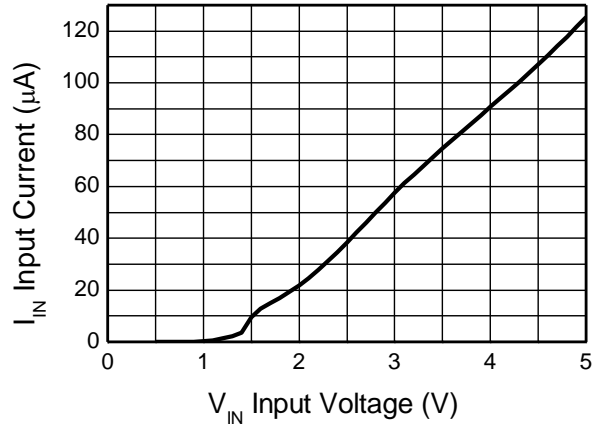
| Characteristic                             | Symbol              | Min  | Typ  | Max | Unit | Test Condition   |
|--|---------------------|------|------|-----|------|--|
| <b>Static Characteristics</b>              |                     |      |      |     |      |  |
| Drain-Source Clamp Voltage                 | V <sub>DS(AZ)</sub> | 60   | 65   | 70  | V    | I <sub>D</sub> = 10mA  |
| Off-State Drain Current                    | I <sub>DSS</sub>    | —    | —    | 500 | nA   | V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V                        |
|  |                     | —    | —    | 1   | μA   | V <sub>DS</sub> = 36V, V <sub>IN</sub> = 0V                        |
| Input Threshold Voltage                    | V <sub>IN(TH)</sub> | 0.7  | 1    | 1.5 | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA           |
| Input Current                              | I <sub>IN</sub>     | —    | 60   | 100 | μA   | V <sub>IN</sub> = +3V  |
|  |                     | —    | 120  | 200 |      | V <sub>IN</sub> = +5V  |
| Input Current while Overtemperature Active | —                   | —    | —    | 220 | μA   | V <sub>IN</sub> = +5V  |
| Static Drain-Source On-State Resistance    | R <sub>DS(ON)</sub> | —    | 400  | 600 | mΩ   | V <sub>IN</sub> = +3V, I <sub>D</sub> = 0.5A                       |
|  |                     | —    | 350  | 500 |      | V <sub>IN</sub> = +5V, I <sub>D</sub> = 0.5A                       |
| Continuous Drain Current (Note 5)          | I <sub>D</sub>      | 0.9  | —    | —   | A    | V <sub>IN</sub> = 3V, T <sub>A</sub> = +25°C                       |
|  |                     | 1.0  | —    | —   |      | V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C                       |
| Continuous Drain Current (Note 6)          |                     | 1.2  | —    | —   |      | V <sub>IN</sub> = 3V, T <sub>A</sub> = +25°C                       |
|  |                     | 1.3  | —    | —   |      | V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C                       |
| Current Limit (Note 8)                     | I <sub>D(LIM)</sub> | 0.7  | 1.7  | —   | A    | V <sub>IN</sub> = +3V  |
|  |                     | 1    | 2.2  | —   |      | V <sub>IN</sub> = +5V  |
| <b>Dynamic Characteristics</b>             |                     |      |      |     |      |  |
| Turn-On Delay Time                         | t <sub>D(ON)</sub>  | —    | 5    | —   | μs   | V <sub>DD</sub> = 12V, I <sub>D</sub> = 0.5A, V <sub>GS</sub> = 5V |
| Rise Time                                  | t <sub>R</sub>      | —    | 10   | —   |      |  |
| Turn-Off Delay Time                        | t <sub>D(OFF)</sub> | —    | 45   | —   |      |  |
| Fall Time                                  | t <sub>F</sub>      | —    | 15   | —   |      |  |
| <b>Overtemperature Protection</b>          |                     |      |      |     |      |  |
| Thermal Overload Trip Temperature (Note 9) | T <sub>JT</sub>     | +150 | +175 | —   | °C   | —  |
| Thermal Hysteresis (Note 9)                | f <sub>F</sub>      | —    | +10  | —   | °C   | —  |

- Notes:
- For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions.
  - For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
  - Thermal resistance from junction and the mounting surfaces of the drain pins.
  - The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on-state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
  - Overtemperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

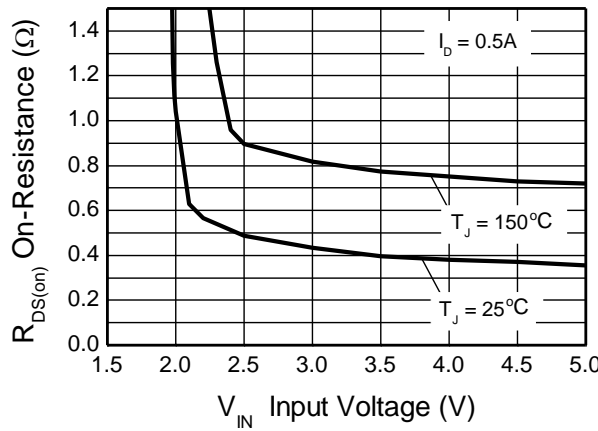
**Typical Performance Characteristics**



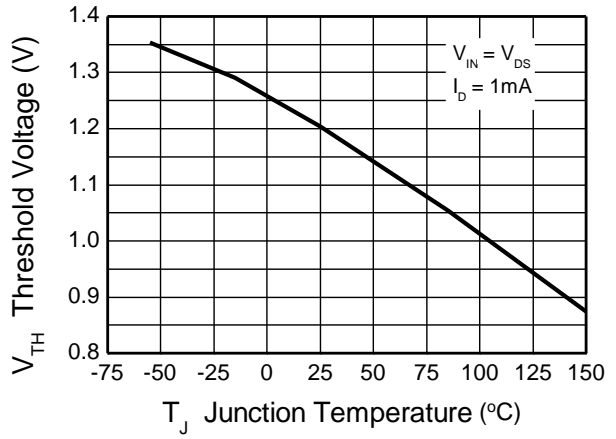
**Typical Output Characteristic**



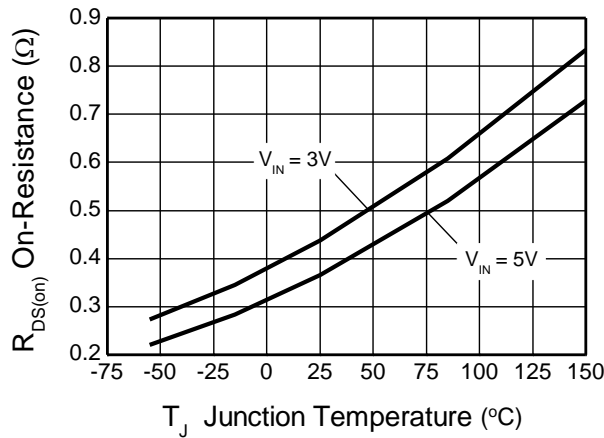
**Input Current vs Input Voltage**



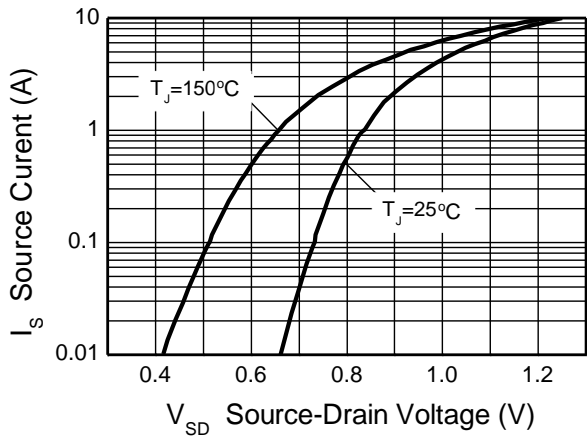
**On-Resistance vs Input Voltage**



**Threshold Voltage vs Temperature**

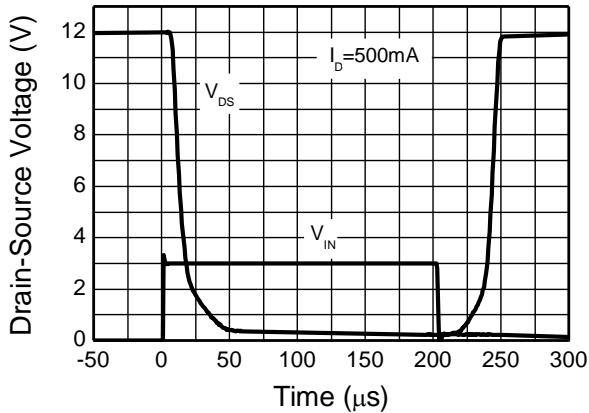


**On-Resistance vs Temperature**

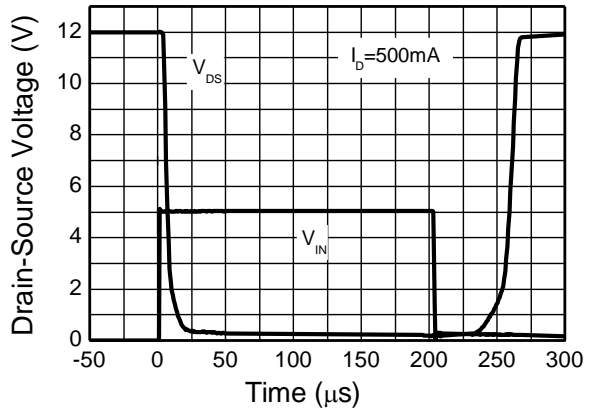


**Reverse Diode Characteristic**

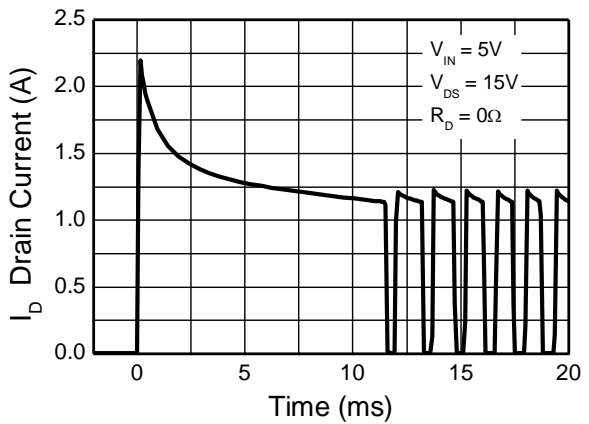
**Typical Performance Characteristics** (continued)



**Switching Speed**



**Switching Speed**

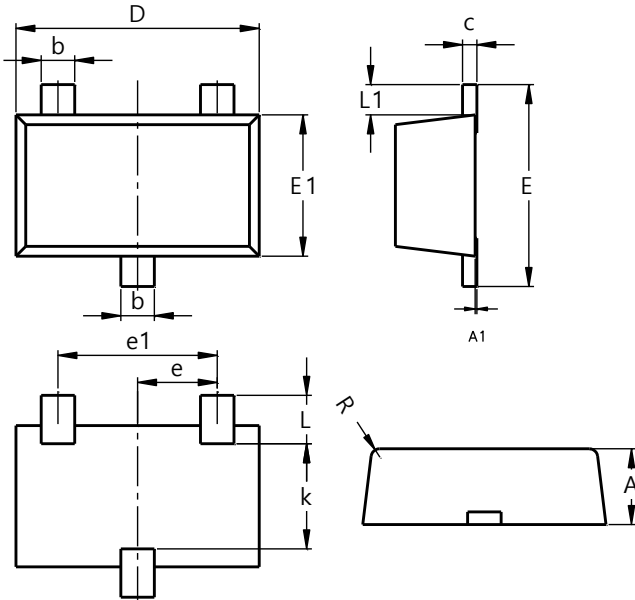


**Typical Short Circuit Protection**

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23F**

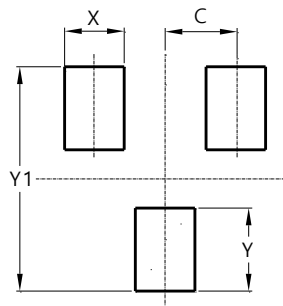


| SOT23F               |          |      |      |
|----------------------|----------|------|------|
| Dim                  | Min      | Max  | Typ  |
| A                    | 0.80     | 1.00 | 0.90 |
| A1                   | 0.00     | 0.10 | 0.01 |
| b                    | 0.35     | 0.50 | 0.44 |
| c                    | 0.10     | 0.20 | 0.16 |
| D                    | 2.80     | 3.00 | 2.90 |
| e                    | 0.95 REF |      |      |
| e1                   | 1.90 REF |      |      |
| E                    | 2.30     | 2.50 | 2.40 |
| E1                   | 1.50     | 1.70 | 1.65 |
| k                    | 1.20     | -    | -    |
| L                    | 0.30     | 0.65 | 0.50 |
| L1                   | 0.30     | 0.50 | 0.40 |
| R                    | 0.05     | 0.15 | -    |
| All Dimensions in mm |          |      |      |

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23F**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.95          |
| X          | 0.80          |
| Y          | 1.110         |
| Y1         | 3.000         |



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[1N4007-T](#) [1N4148-T](#) [1N4148W-13-F](#) [1N4148W-7-F](#) [1N4148WQ-13-F](#) [1N4148WQ-7-F](#) [1N4148WS-13-F](#) [1N4148WS-7-F](#) [1N4148WSF-7](#)